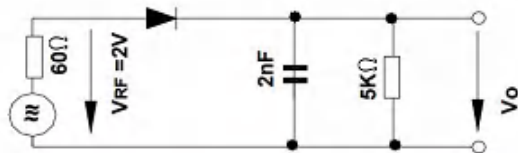


FEATURES

Fast switching diode in MiniMELF case especially suited for automatic surface mounting.



Rectification Efficiency Measurement Circuit



LL-34



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
at $t = 1$ s		1	
at $t = 1$ ms		4	
at $t = 1$ μ s			
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

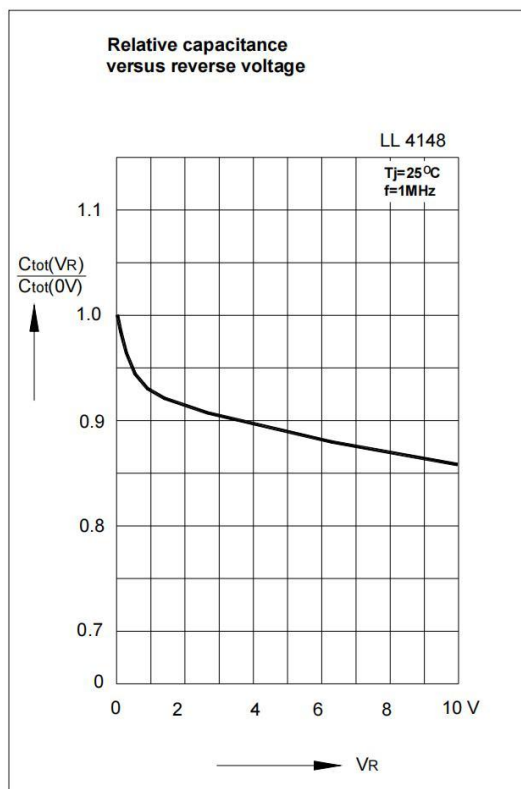
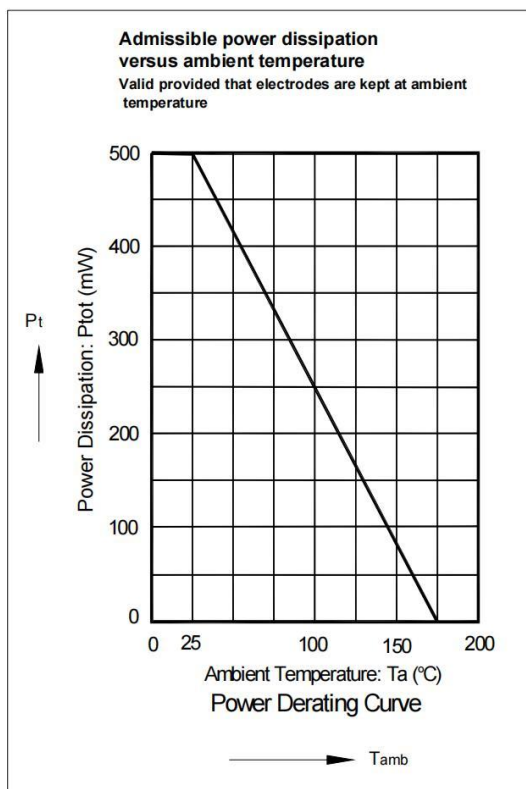
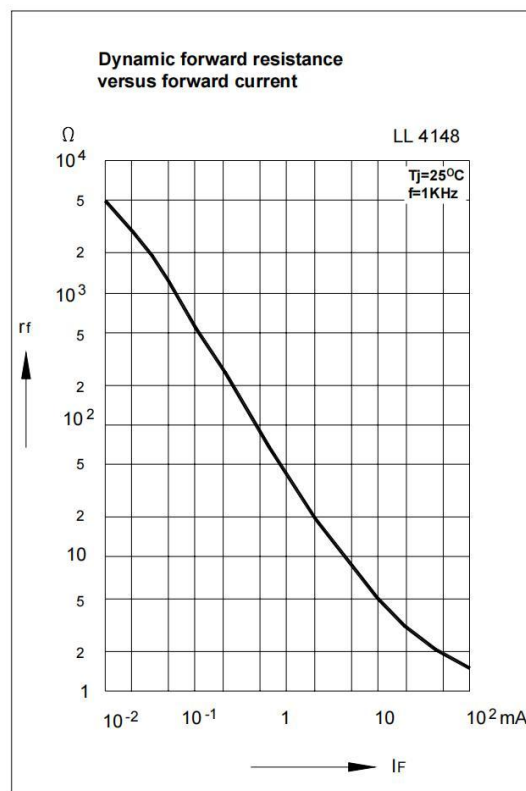
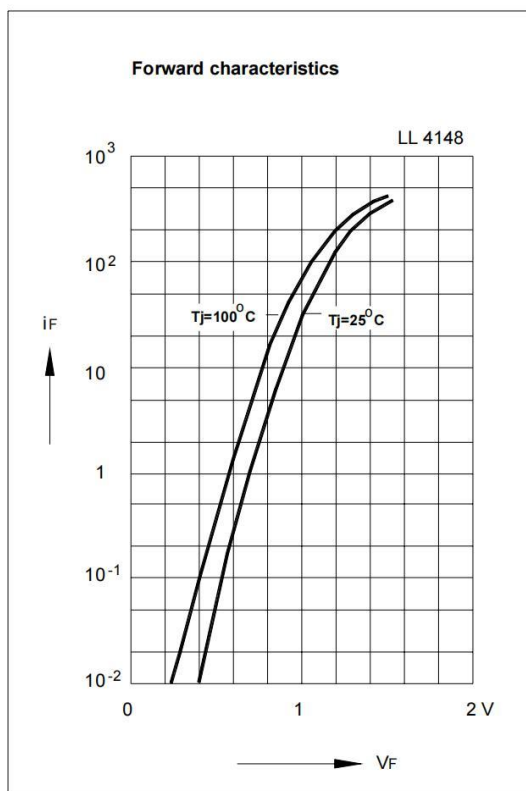
¹⁾ Valid provided that electrodes are kept at ambient temperature.

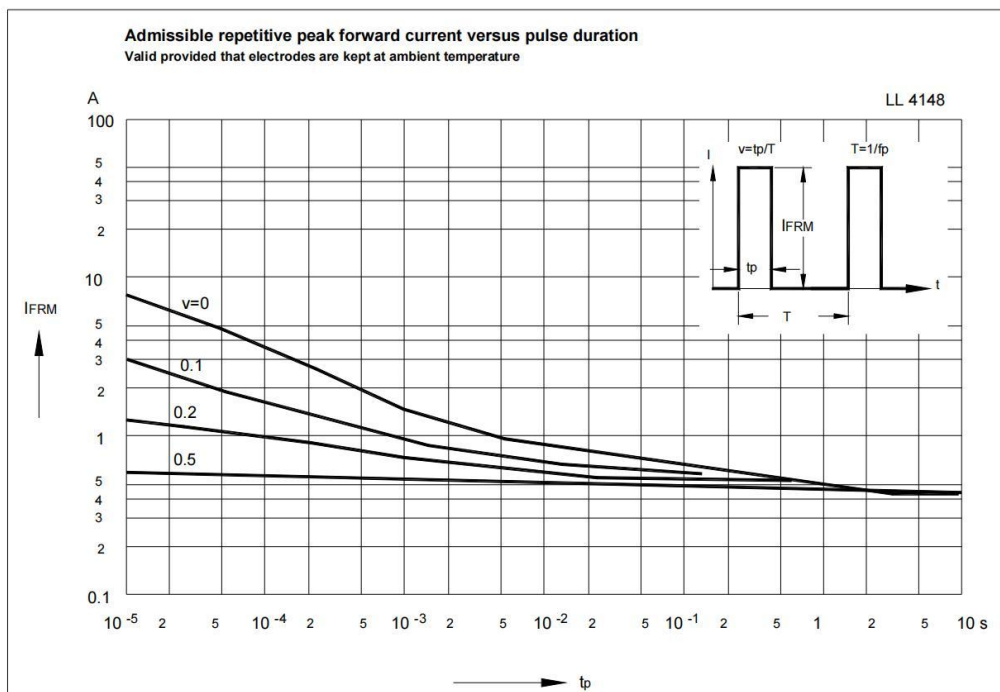
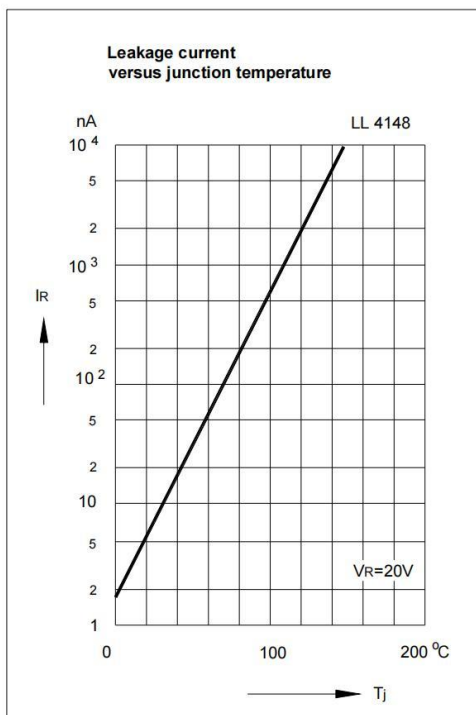
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10$ mA	V_F	-	1	V
Leakage Current at $V_R = 20$ V	I_R	-	25	nA
at $V_R = 75$ V	I_R	-	5	μ A
at $V_R = 20$ V, $T_j = 150^\circ\text{C}$	I_R	-	50	μ A
Reverse Breakdown Voltage tested with 100 μ A Pulses	$V_{(BR)R}$	100	-	V
Capacitance at $V_R = 0$, $f = 1$ MHz	C_{tot}	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses $t_p = 0.1$ s, Rise Time < 30 ns, $f_p = 5$ to 100 KHz	V_{fr}	-	2.5	V
Reverse Recovery Time at $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100$ Ω	t_{rr}	-	4	ns
Thermal Resistance Junction to Ambient Air	R_{thA}	-	0.35 ¹⁾	K/mW
Rectification Efficiency at $f = 100$ MHz, $V_{RF} = 2$ V	η_V	0.45	-	-

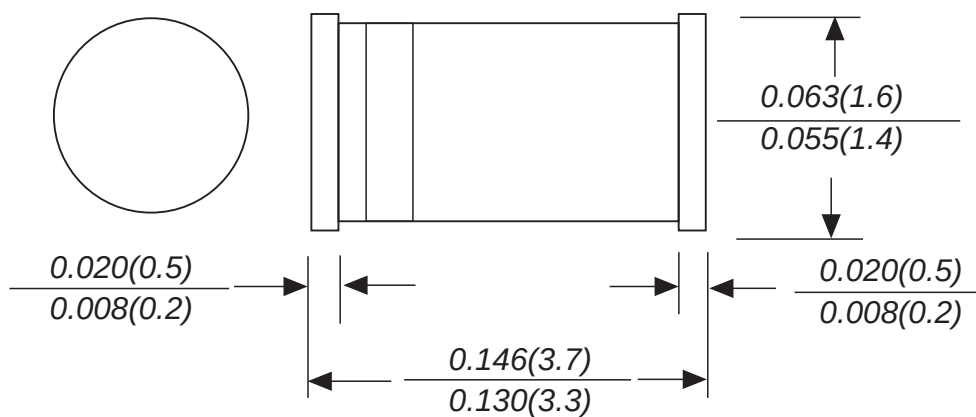
¹⁾ Valid provided that electrodes are kept at ambient temperature.

Typical Characteristics





LL-34 Package Information



Dimensions in inches and (millimeters)